

POSTER SESSION TUESDAY

	Last Name	First Name	Laboratory	Country	Title
Tu.1	Anjum	Taseer	Universität Siegen	Germany	Lattice thermal expansion of as-grown GaAs nanowires due to optical excitation measured by X-ray pump probe
Tu.2	Arya	Chaitanya	University of Basel	Switzerland	Phononic and thermal properties of InAsSb twin superlattices nanowires
Tu.3	Ayuso Perez	Irene	Paul-Drude-Institut	Germany	Contacting GaAs/AlxGa1-xAs core-shell nanowires: a transport and cathodoluminescence study
Tu.4	Böckle	Raphael	TU Wien	Austria	Low-frequency Noise in Room-temperature quasi-ballistic Ge NW Transistors
Tu.5	Jeong	Hyowon	Walter Schottky Institut	Germany	Narrow near band-edge emission from phase-pure non-VLS GaAsSb NWs
Tu.6	Mattiat	Hinrich	University of Basel	Switzerland	Nanowires as mechanical force sensors for scanning probe microscopy
Tu.7	Oliva	Miriam	Paul-Drude-Institut	Germany	Photoluminescence spectroscopy of ordered arrays of thin, top-down fabricated GaN/(In,Ga)N nanowires
Tu.8	Paul	Rajrupa	EPFL	Switzerland	Tailoring Hall bars of Zn3P2 grown on InP to understand its electrical properties
Tu.9	Repp	Daniel	Universität Jena	Germany	Numerical parameter study of Purcell factor enhancement and lasing threshold for semiconductor nanowires coupled to planar metals
Tu.10	Van Lange	Victor	Eindhoven Univ. Technology	Netherlands	Nanosecond radiative lifetime from Hex-Ge
Tu.11	Lampadaris	Charalampos	University of Copenhagen	Danemark	Capped InAs SAG gate-tunable nanowires
Tu.12	Prete	Domenic	NEST Scuola Normale Superiore	Italy	Impact of electrostatic doping on carrier concentration and mobility in InAs nanowires
Tu.13	Vezzosi	Andrea	Univ. Modena Reggio Emilia	Italy	Band structure of modulation-doped core-shell nanowires
Tu.14	Hynes	Michael	University College London	United Kingdom	Zeeman field in InAs nanowires using micromagnet arrays
Tu.15	Vekris	Alexandros	University of Copenhagen	Danemark	Coulomb blockade in double-nanowire superconducting islands
Tu.16	Witmans	Femke	University of Twente	Netherlands	Two approaches for topological superconductivity in nanowires
Tu.17	Aziz	Daniel	Georgia Inst. of Technology	USA	Bottom-up Nanoscale Patterning and Selective Deposition on Semiconductor Nanowires
Tu.18	Barker	David	Lund University	Sweden	Work fluctuations and dissipation in information engines based on InAs nanowires
Tu.19	Hijazi	Hadi	CNRS-LTM	France	VLS Growth of GaSe Nanoribbons by MOCVD for Photodetection Applications
Tu.20	Jeddi	Hossein	Lund University	Sweden	Gain and bandwidth of InP nanowire array photodetectors with embedded photogated InAsP quantum discs
Tu.21	Alcer	David	Lund University	Sweden	Correlated light-beam induced current and photoluminescence mapping on large area nanowire photovoltaic devices
Tu.22	Kolpakov	Ilya	Eindhoven Univ. Technology	Netherlands	Voltage losses in top-down fabricated nanowire solar cell
Tu.23	Tong	Capucine	IPVF	France	Luminescence as a valuable characterization tool from single III-V nanowires to complete solar cells
Tu.24	Blaga	Claire	EPFL	Switzerland	Using nanowires to increase the cathodoluminescence intensity of 2D materials
Tu.25	Manrique	Manuel	LTM - LMGP - CEA Leti	France	Chemical bath deposition of ZnO nanowires on Au seed layers for piezoelectric nanogenerators
Tu.26	Pantle	Florian	Walter Schottky Institut	Germany	Influence of environmental conditions and surface treatments on the photoluminescence properties of GaN nanowires and nanofins
Tu.27	Jose	Anitha	Simon Fraser University	Canada	Mapping electrostatic potential gradient in GaN NW p-n junctions using electron holography
Tu.28	Fiordaliso	Elisabetta Maria	Technical Univ. of Denmark	Danemark	In-situ off-axis electron holography of real-time dopant diffusion in GaAs NWs
Tu.29	Zannier	Valentina	Nanoscience Institute CNR	Italy	Growth and Raman spectroscopy of GaAs/GaP superlattice nanowires
Tu.30	Vettori	Marco	Eindhoven Univ. Technology	Netherlands	Au-free GaAs/hex-Ge core/shell nanowires on Si substrates for photonic integration
Tu.31	Van den Berg	Theo	C2N Universite Paris Saclay	France	Allotropism and twinning in top-down etched silicon nanowires
Tu.32	Patel	Nikesh	University of Manchester	United Kingdom	High Intra- and Interwire uniformity in 2D Radial GaAsP/GaAs Core/Shell Triple Quantum Well Structures
Tu.33	Lähnemann	Jonas	Paul-Drude-Institut	Germany	Emission from InGaAs segments on GaAsSb nanowires
Tu.34	Kalt	Jochen	Karlsruhe Inst. of Technology	Germany	Reversed nanowire bending in GaAs/(In,Ga)As/GaAs heterostructures
Tu.35	Hilliard	Donovan	Helmholtz-Zentrum Dresden-Rossendorf	Germany	Enhancing the interface sharpness of axial heterostructures in self-catalyzed nanowires
Tu.36	Durand	Christophe	CEA Grenoble	France	Core-shell InGaN quantum wells: defect-free growth and dual color emission
Tu.37	Concordel	Alexandre	CEA Grenoble	France	The issues of non-radiative recombination centres in InGaN/GaN nanowires elaborated by MBE
Tu.38	Dede	Didem	EPFL	Switzerland	Selective Area Epitaxy: Growth Mechanisms and Geometrical Constraints
Tu.39	Zhuang	Qiandong	Lancaster University	United Kingdom	GaSb Quantum Dots in GaAs Nanowire for Single Photon Emission
Tu.40	Vazquez-Pufleau	Miguel	IMDEA Materials	Spain	Automation in Characterization of Reactors for Continuous Nanowire Growth in the Gas Phase
Tu.41	Peeters	Wouter	Eindhoven Univ. Technology	Netherlands	Growth of Au-catalyzed wurtzite GaAs on masked GaAs substrates
Tu.42	Karlinger	Monika	Walter Schottky Institut	Germany	Crystal side-facet tuning of GaN nanowires and nanofins on AlN templates
Tu.43	Kang	Jingxuan	Paul-Drude-Institut	Germany	Controlling the dimensions of top-down GaN nanowire ensembles via self-assembled metal islands
Tu.44	Jung	Jason	Eindhoven Univ. Technology	Netherlands	Universal Platform for Scalable Semiconductor-Superconductor Nanowire Networks
Tu.45	Hu	Tianyi	Lund University	Sweden	Switching between different Growth Modes in Cu-seeded GaP Nanowires
Tu.46	Hoskam	Max	Eindhoven Univ. Technology	Netherlands	Charge carrier density tuning towards the topological regime in MBE grown Pb1-xSnxTe nanowires
Tu.47	Forrer	Nicolas	University of Basel	Switzerland	Germanium-Silicon Core-Shell Nanowires for Spin/Hole Qubits fabricated by Chemical Vapour Deposition

Tu.48	Da Silva	Bruno	CNRS-Institut Néel	France	Ni-catalyzed growth of GaP nanowires and nanosheets
Tu.49	Chereau	Emmanuel	Univ. Clermont- Institut Pascal	France	III-As nanowire arrays grown by HVPE
Tu.50	Bosch	Julien	CNRS-CRHEA	France	Etching of the SiNx passivation layer for extended shell coverage in InGaN/GaN core shell nanowire
Tu.51	Bassani	Franck	CNRS-LTM	France	Chemical composition control of (Si)GeSn nanowires by VLS -CVD
Tu.52	Barth	Sven	Goethe University Frankfurt	Germany	Metastable Ge-based nanowire materials
Tu.53	Baillard	Adrien	Grenoble INP LMGP	France	Al and Ga co-doping of ZnO nanowires grown by chemical bath deposition
Tu.54	Alattallah	Khalifah	University of Copenhagen	Danemark	Development of InSb-Pb hybrid nanowire material platform